




Lecture1: Basic physics of semiconductors

Sung-Min Hong (smhong@gist.ac.kr)

Semiconductor Device Simulation Lab.
School of Electrical Engineering and Computer Science
Gwangju Institute of Science and Technology

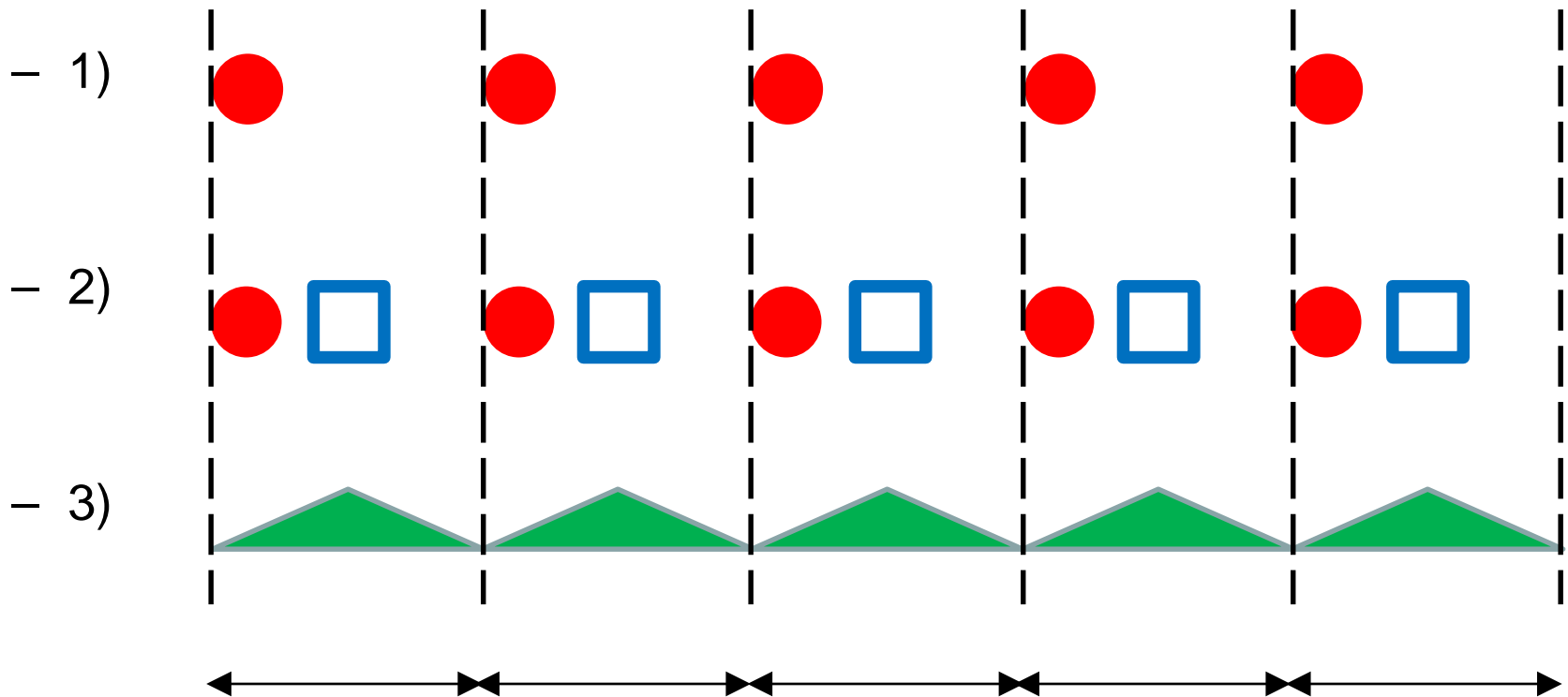
Periodicity

- Find one with a different period. (They are 1D patterns.)

- 1) 
- 2) 
- 3) 
- 4) 

Why did I ask it?

- You can easily find the correct solution!



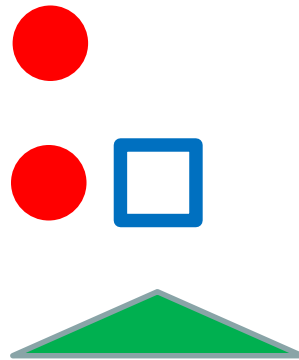
- They DO share the period. However, they look different.

Now you understand that

- We have to distinguish two different quantities.
 - Periodic array of points (“Lattice” in our terminology)



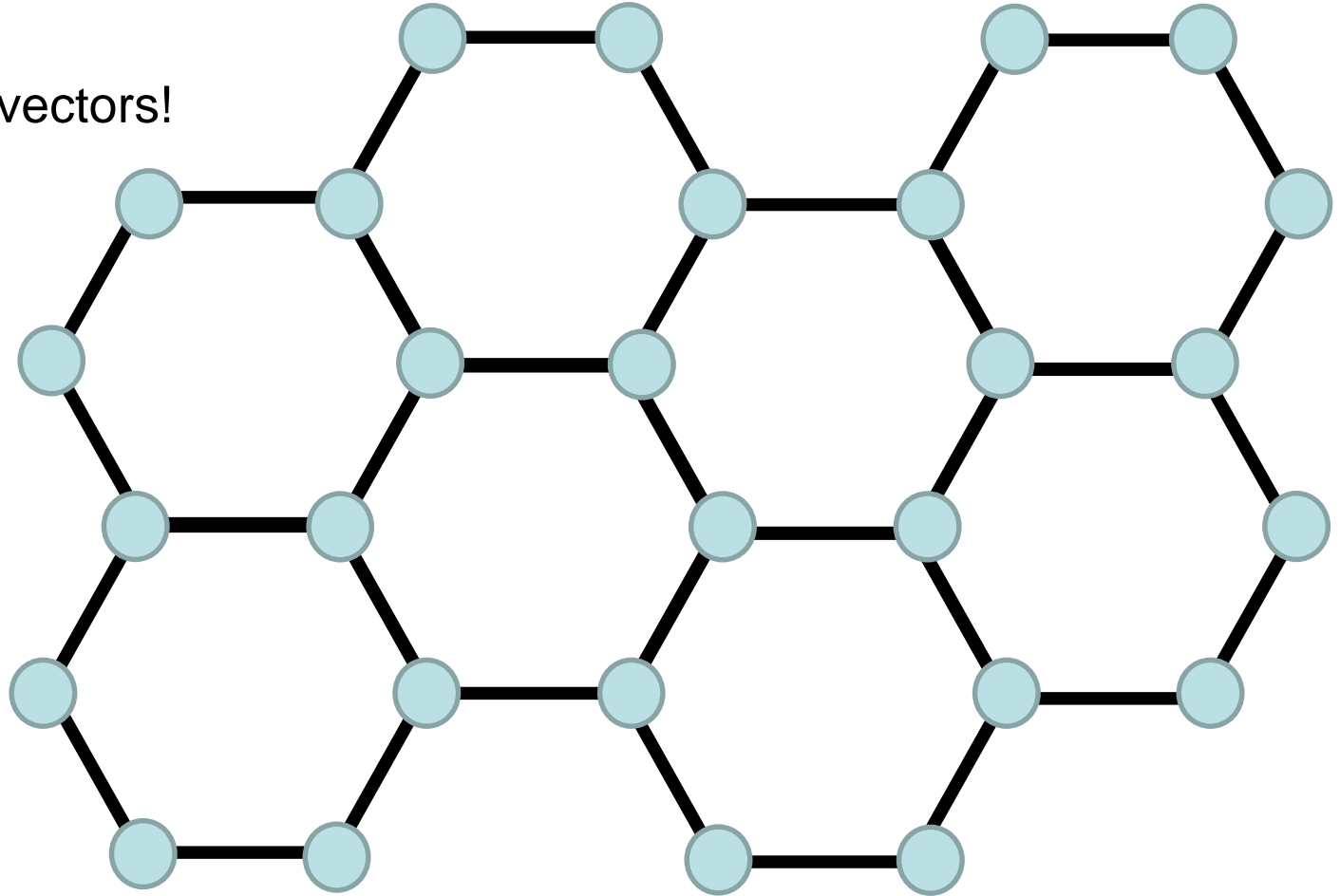
- Pattern to be repeated (“Basis” in our terminology)



- Non-trivial 2D example?

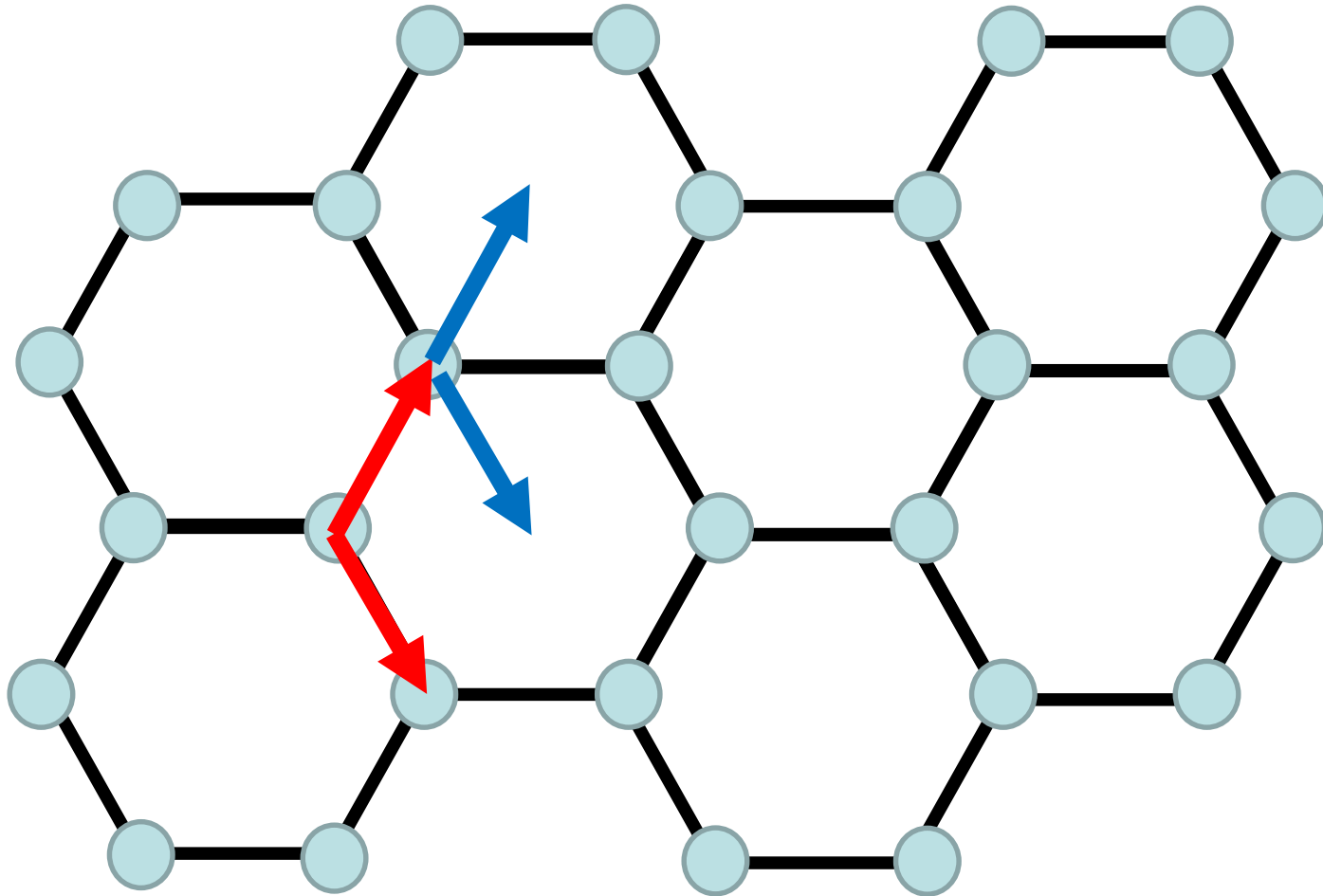
Graphene

- Single layer of carbon atoms in a 2D hexagonal lattice.
 - Find two vectors!



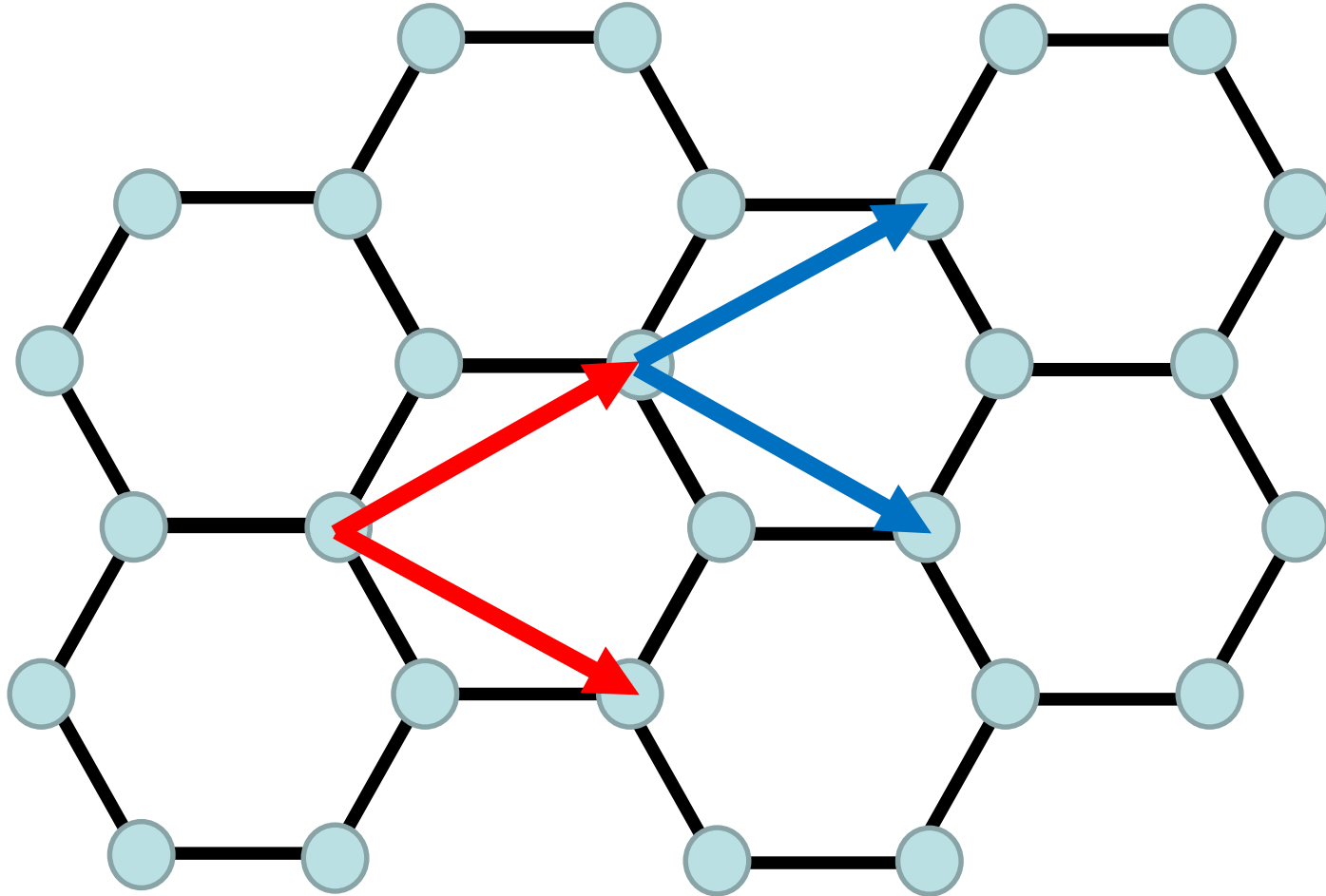
First trial

- A wrong answer!



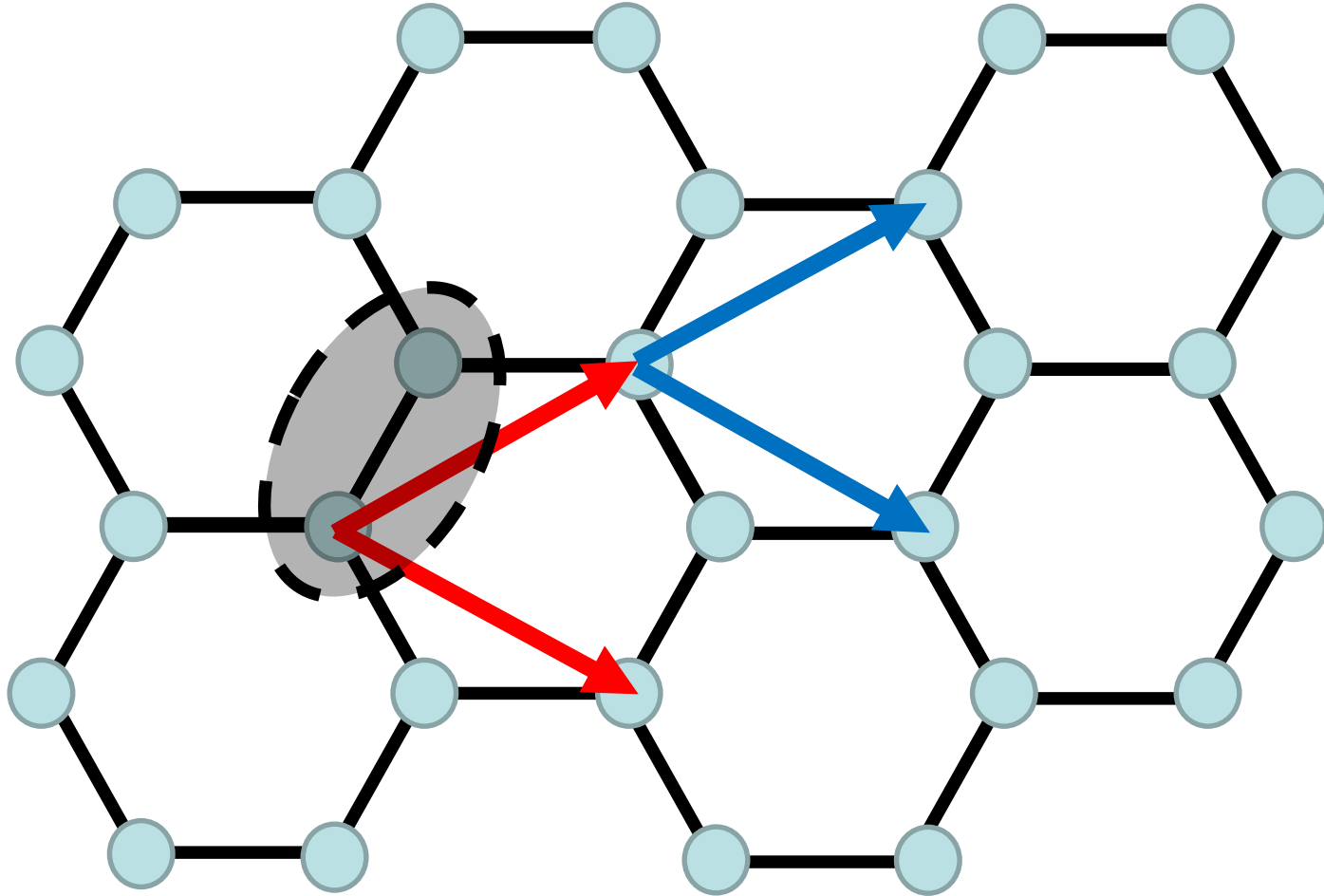
Lattice vectors

- Vectors connecting the second nearest neighbors.



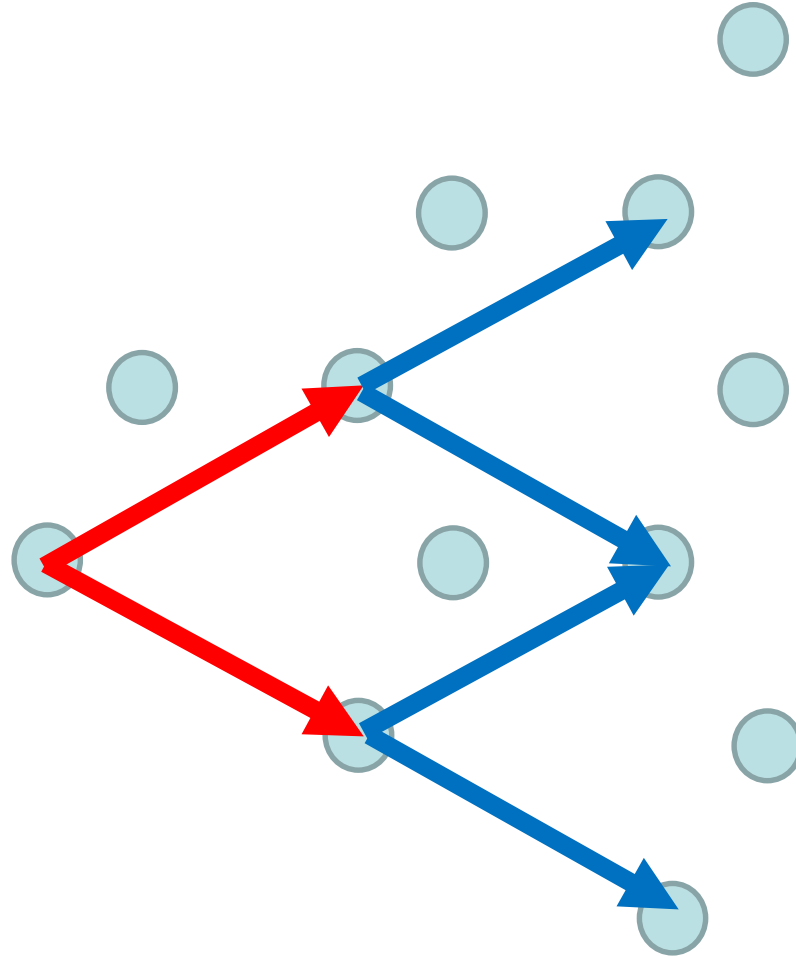
Basis

- Two neighboring atoms consist of the basis.



Basis

- Two neighboring atoms consist of the basis.



Silicon

- Atomic number: 14

Group Period →	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	18
1	1 H																	2 He
2	3 Li	4 Be											5 B	6 C	7 N	8 O	9 F	10 Ne
3	11 Na	12 Mg											13 Al	14 Si	15 P	16 S	17 Cl	18 Ar
4	19 K	20 Ca	21 Sc	22 Ti	23 V	24 Cr	25 Mn	26 Fe	27 Co	28 Ni	29 Cu	30 Zn	31 Ga	32 Ge	33 As	34 Se	35 Br	36 Kr
5	37 Rb	38 Sr	39 Y	40 Zr	41 Nb	42 Mo	43 Tc	44 Ru	45 Rh	46 Pd	47 Ag	48 Cd	49 In	50 Sn	51 Sb	52 Te	53 I	54 Xe
6	55 Cs	56 Ba	57 La	* 72 Hf	73 Ta	74 W	75 Re	76 Os	77 Ir	78 Pt	79 Au	80 Hg	81 Tl	82 Pb	83 Bi	84 Po	85 At	86 Rn
7	87 Fr	88 Ra	89 Ac	* 104 Rf	105 Db	106 Sg	107 Bh	108 Hs	109 Mt	110 Ds	111 Rg	112 Cn	113 Nh	114 Fl	115 Mc	116 Lv	117 Ts	118 Og
				* 58 Ce	59 Pr	60 Nd	61 Pm	62 Sm	63 Eu	64 Gd	65 Tb	66 Dy	67 Ho	68 Er	69 Tm	70 Yb	71 Lu	
				* 90 Th	91 Pa	92 U	93 Np	94 Pu	95 Am	96 Cm	97 Bk	98 Cf	99 Es	100 Fm	101 Md	102 No	103 Lr	

Periodic table (Wikipedia)

Face-centered cubic (fcc)

- Lattice points of the simple cubic lattice
 - For example, (assuming the edge length of 1)

$(0, 0, 0)$

$(1, 0, 0)$ $(0, 1, 0)$ $(0, 0, 1)$

$(1, 1, 0)$ $(1, 0, 1)$ $(0, 1, 1)$

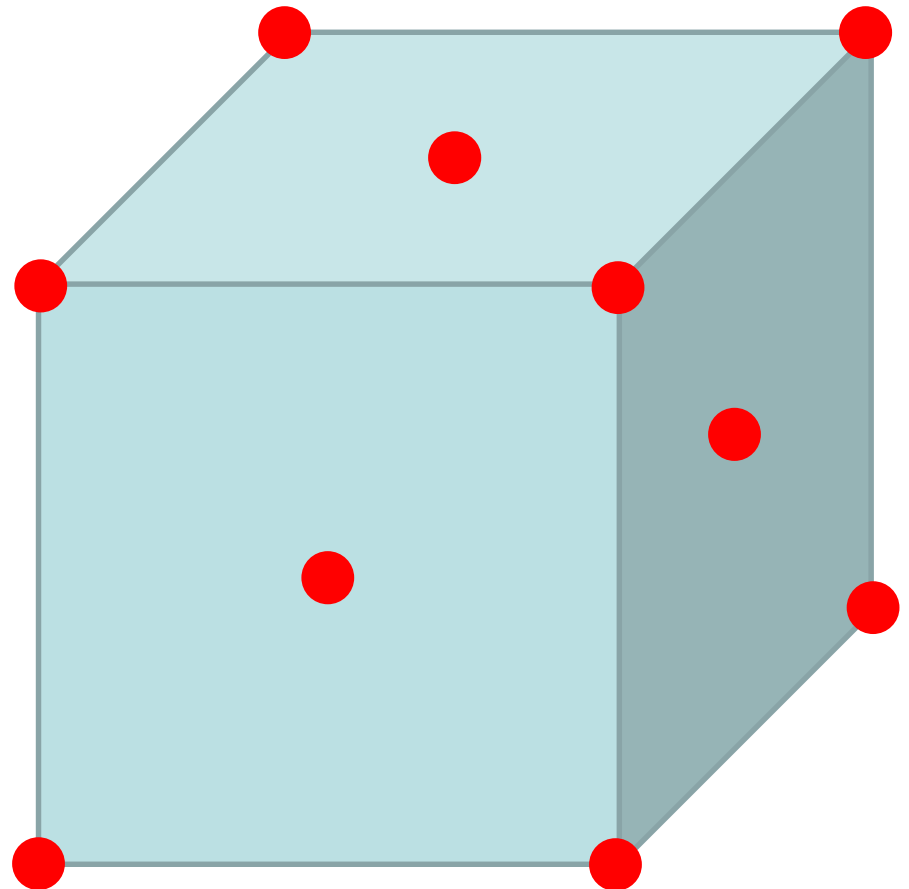
$(1, 1, 1)$

- Lattice points at all faces
 - For example,

$(0.5, 0.5, 0)$

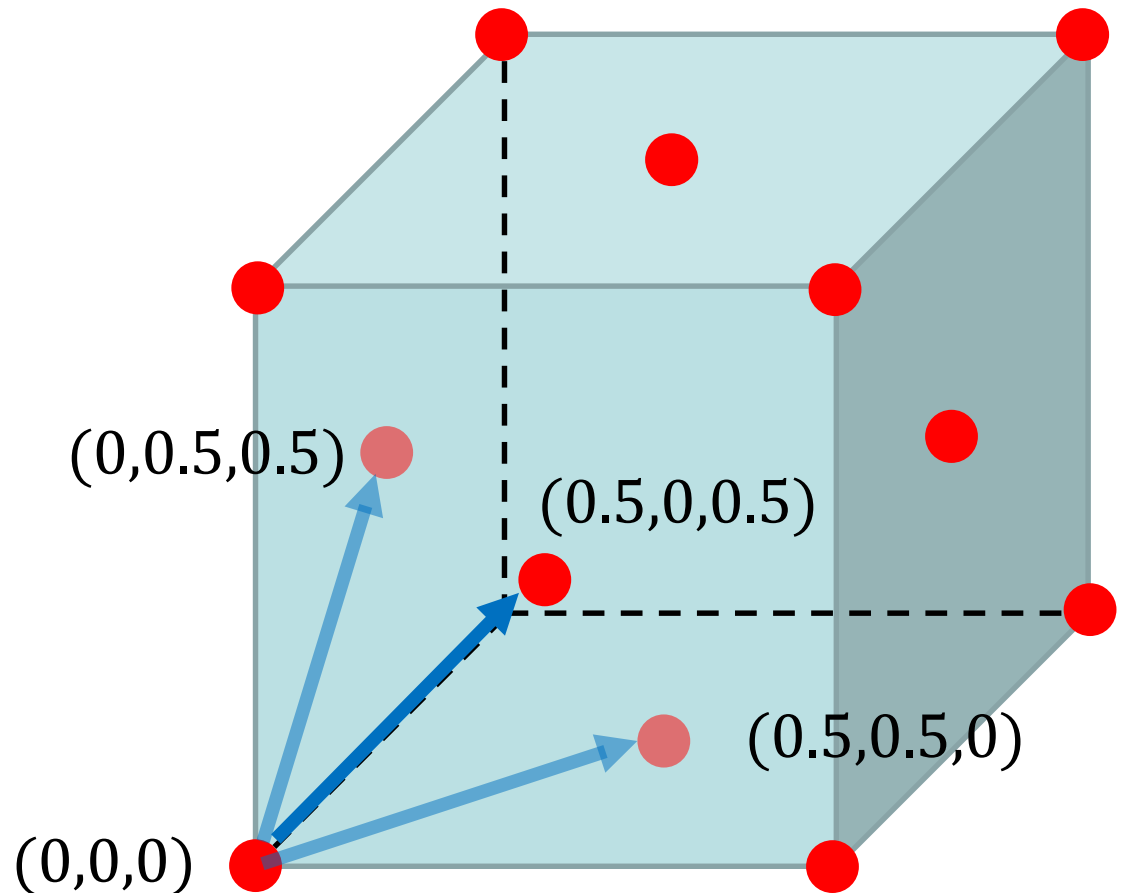
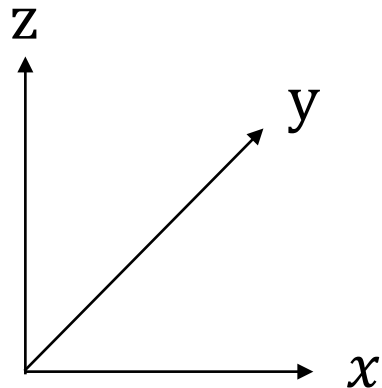
$(0.5, 0, 0.5)$

$(0, 0.5, 0.5)$



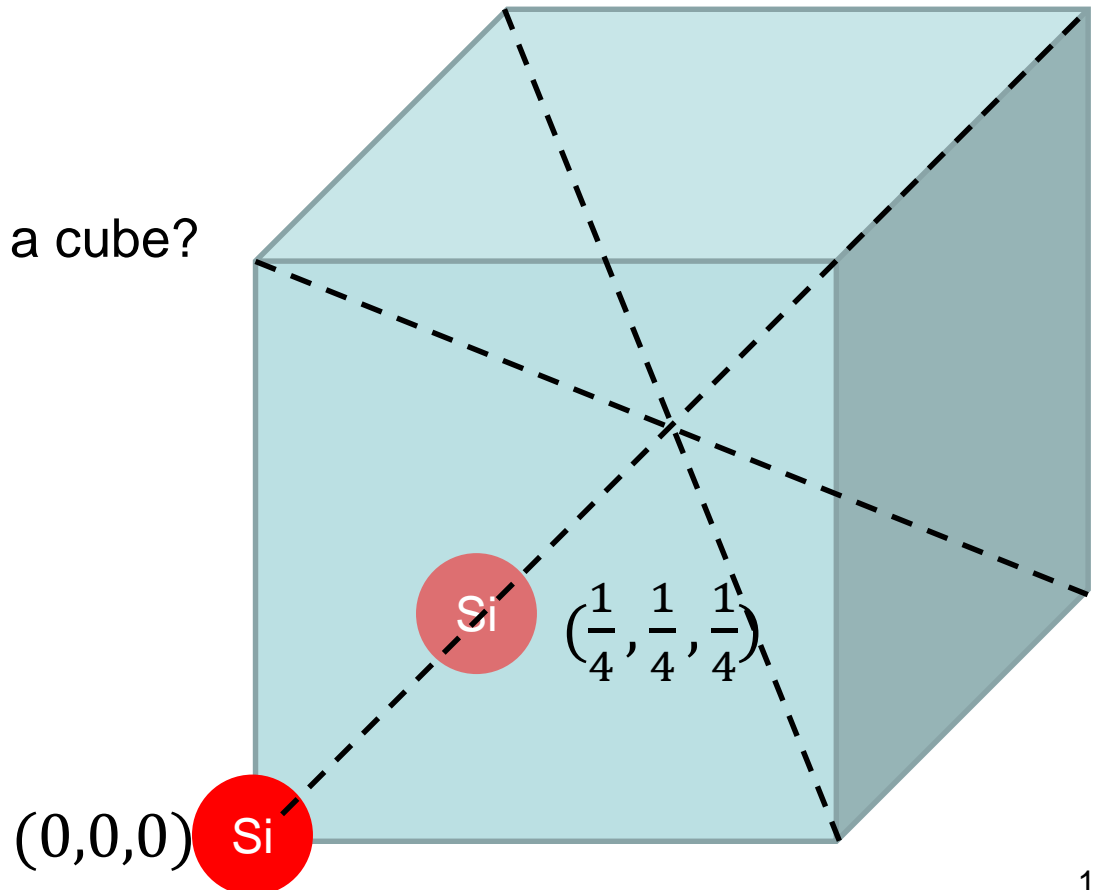
Lattice vectors

- Three vectors connecting the nearest neighbors.
 - They are
 $(0.5, 0.5, 0)$
 $(0.5, 0, 0.5)$
 $(0, 0.5, 0.5)$



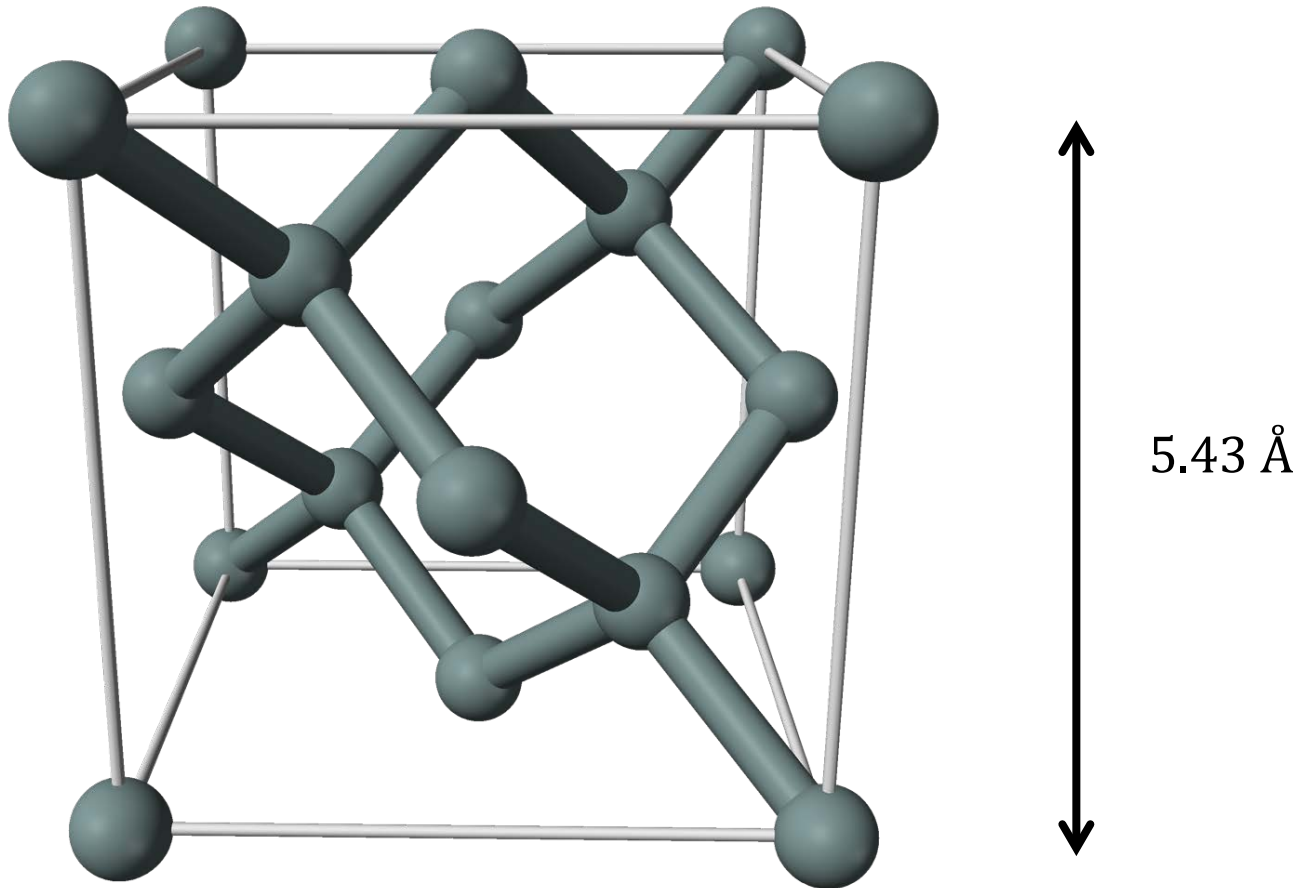
Basis

- Two silicon atoms
 - When an atom is placed at $(0, 0, 0)$, position of the other one is $(0.25, 0.25, 0.25)$.
- Question
 - How many atoms in a cube?



Crystal structure of Si

- Diamond cubic crystal structure



Diamond cubic crystal structure (Wikipedia)

Free electron

- Wavefunction, ψ

- We want to know $\psi(\mathbf{r}, t)$.

- When the potential is constant, we simply have

$$\psi(\mathbf{r}, t) \propto \exp\left(i\left(\mathbf{k} \cdot \mathbf{r} - \frac{E}{\hbar} t\right)\right)$$

- A wave propagating along the direction of \mathbf{k}

- Question) When time is increased by δt , where can we find a point with the same phase?

At $t = t_0 + \Delta t$, $\mathbf{r} = \mathbf{r}_0 + ?$



At $t = t_0$, $\mathbf{r} = \mathbf{r}_0$.

Velocity

- When the displacement is $\Delta \mathbf{r}$,

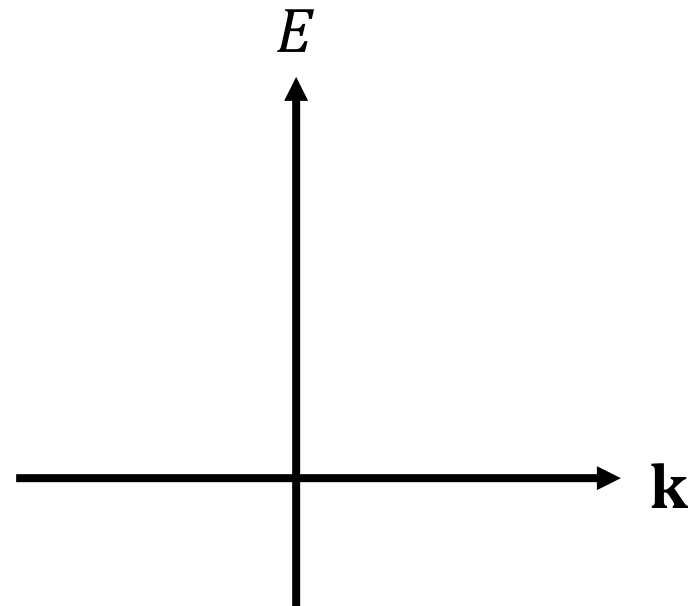
$$\mathbf{k} \cdot \Delta \mathbf{r} - \frac{E}{\hbar} \Delta t = 0$$

- Direction: The direction of \mathbf{k}
- Distance during Δt :

$$\frac{|\Delta \mathbf{r}|}{\Delta t} = \frac{1}{\hbar} \frac{E}{|\mathbf{k}|}$$

- Velocity of a free electron

- Energy, E
- Wave vector, \mathbf{k}

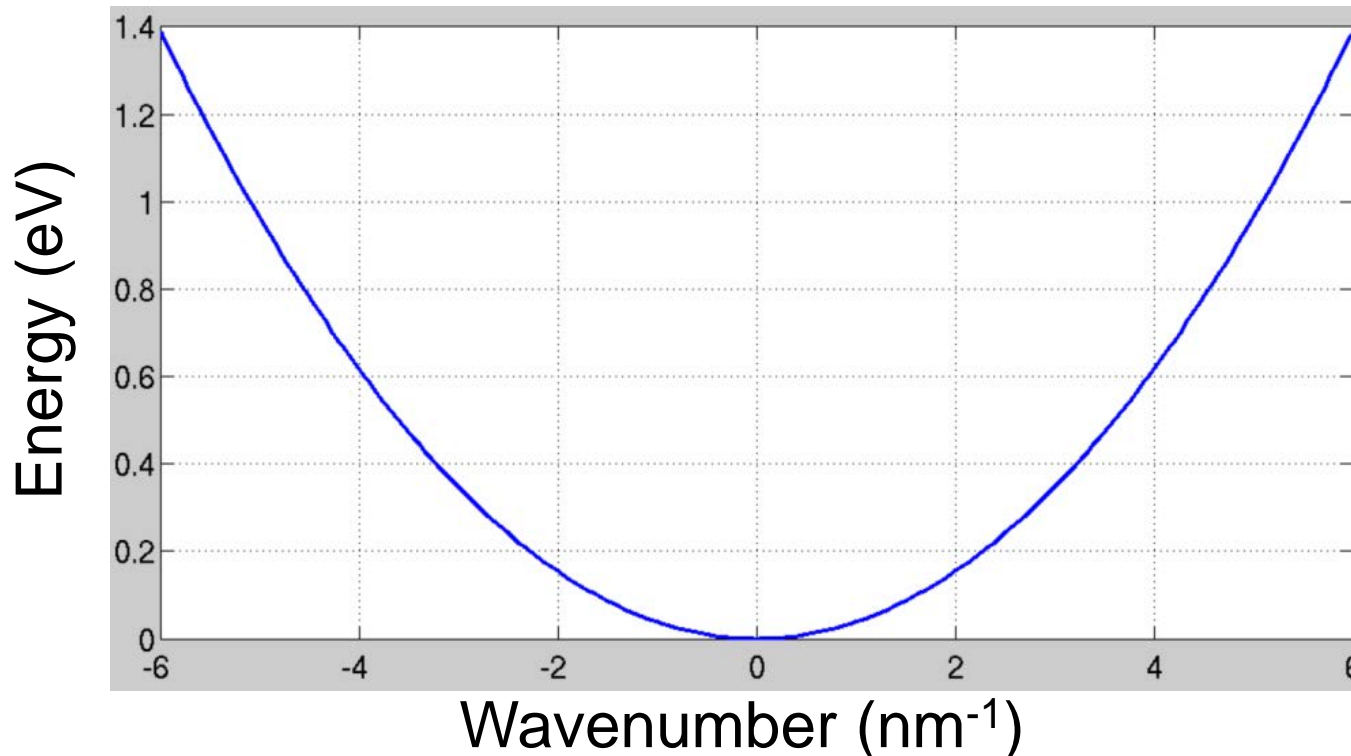


$E - \mathbf{k}$ relation

- Parabolic relation

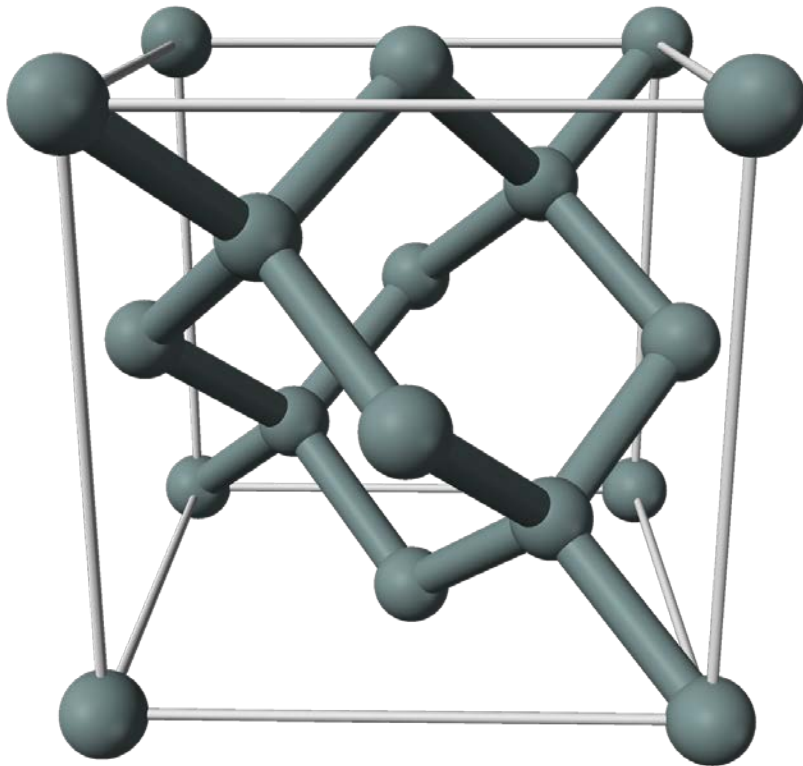
$$E = \frac{\hbar^2}{2m} |\mathbf{k}|^2$$

- Can you see the gap?

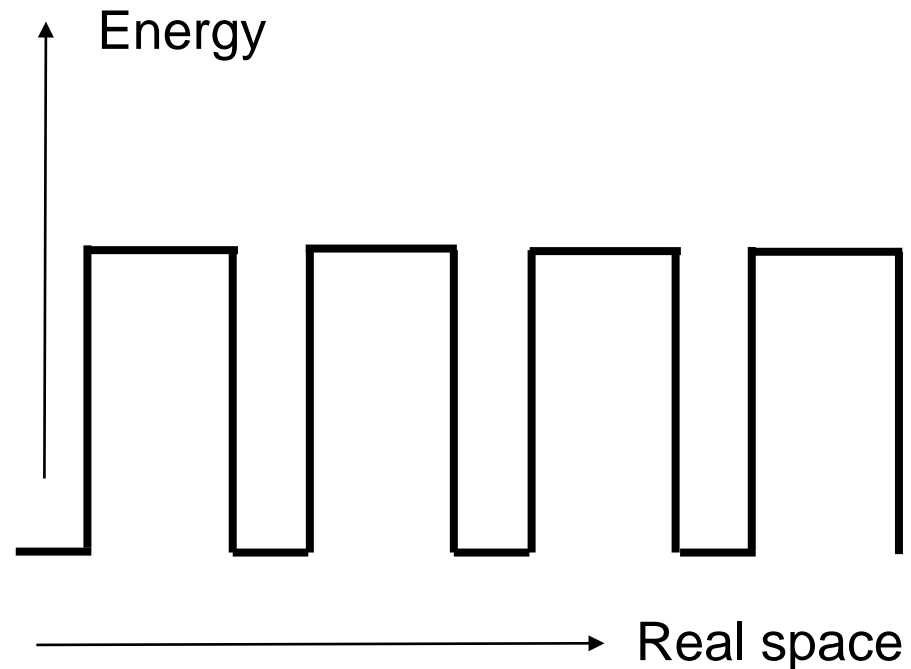


Periodic potential

- Atomic cores are positively charged.
 - Electrons are attracted by them.
 - Potential energy is PERIODICALLY modulated.



Diamond cubic crystal structure (Wikipedia)

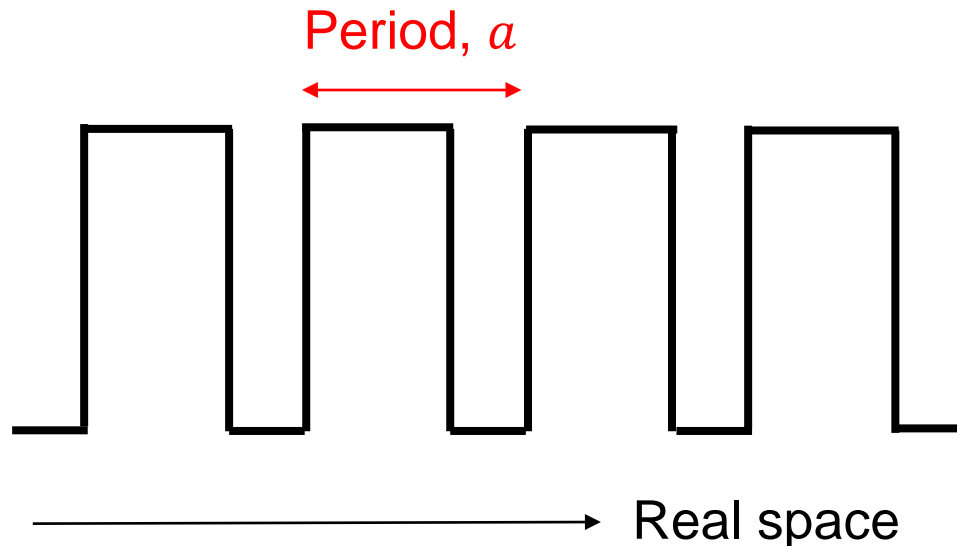


Expansion

- Periodic function can be expanded.
 - With a period of a , the potential energy can be expressed as

$$V(x) = V_0 + \sum_{n=1}^{\infty} V_{c,n} \cos\left(n \frac{2\pi}{a} x\right) + V_{s,n} \sin\left(n \frac{2\pi}{a} x\right)$$

- Simplest example) $V(x) = V_{c,1} \cos\left(\frac{2\pi}{a} x\right)$



Coupling

- Now, the potential contains $\exp\left(i\frac{2\pi}{a}x\right)$ and $\exp\left(-i\frac{2\pi}{a}x\right)$.
 - Therefore, an operation of $V\psi$ on a free electron, $\exp(ikx)$, yields

$$\exp\left(i\left(k + \frac{2\pi}{a}\right)x\right)$$

and

$$\exp\left(i\left(k - \frac{2\pi}{a}\right)x\right)$$

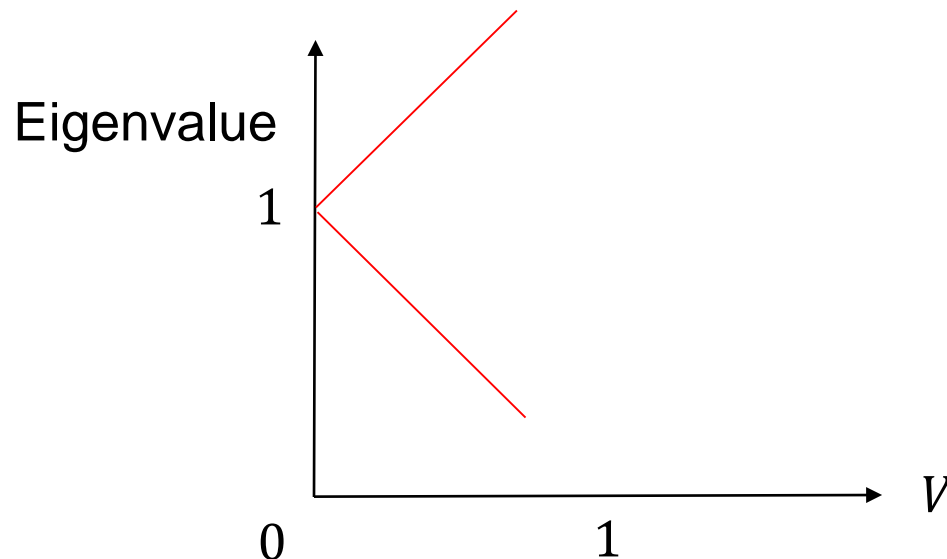
- When $k = \frac{\pi}{a}$, we have the coupling between $\exp\left(i\frac{\pi}{a}x\right)$ and $\exp\left(-i\frac{\pi}{a}x\right)$.
 - And they have the same energy!

A simple eigenvalue problem

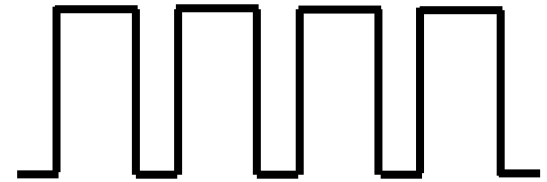
- Solve a simple eigenvalue problem.

$$\begin{bmatrix} 1 & V \\ V & 1 \end{bmatrix} \begin{bmatrix} x_1 \\ x_2 \end{bmatrix} = \lambda \begin{bmatrix} x_1 \\ x_2 \end{bmatrix}$$

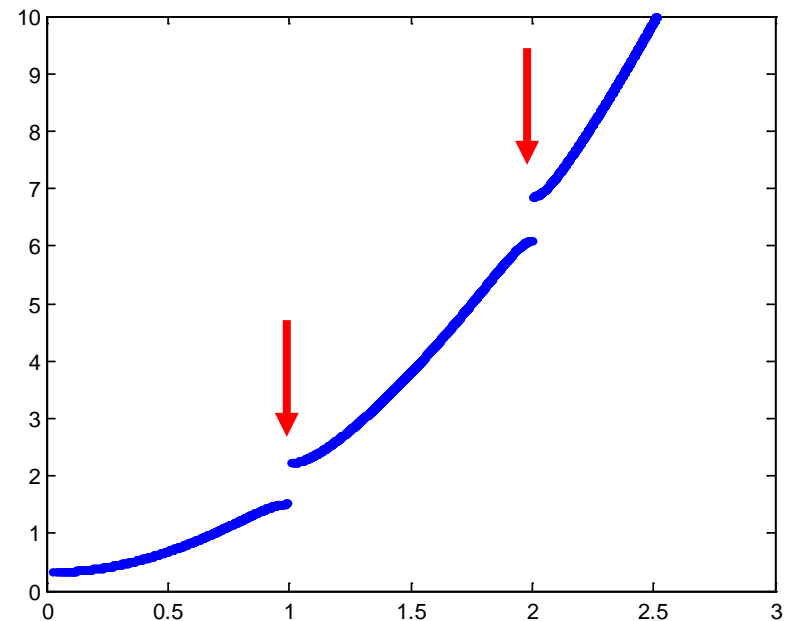
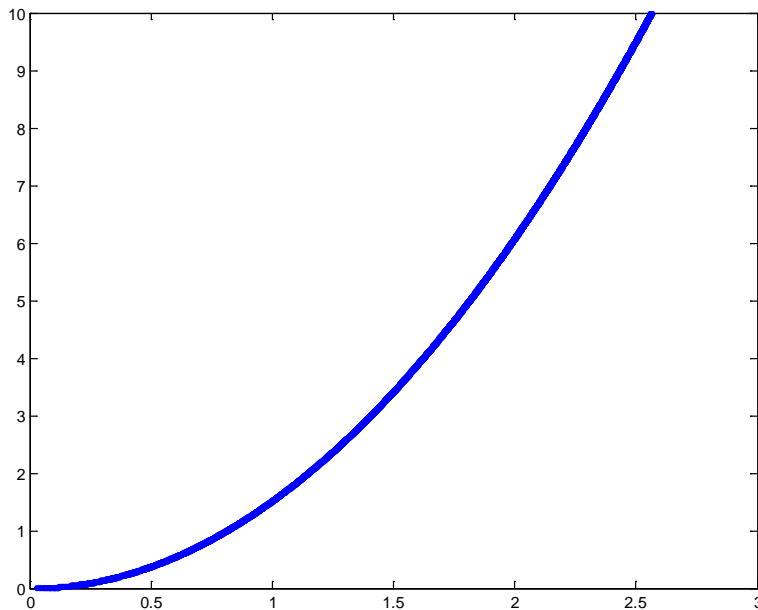
- Of course, when $V = 0$, two eigenvalues are 1.
- When $V \neq 0$, two eigenvalues are $1 + V$ and $1 - V$.
- Two eigenvectors are $\begin{bmatrix} 1 \\ 1 \end{bmatrix}$ and $\begin{bmatrix} 1 \\ -1 \end{bmatrix}$.



Kronig-Penny model

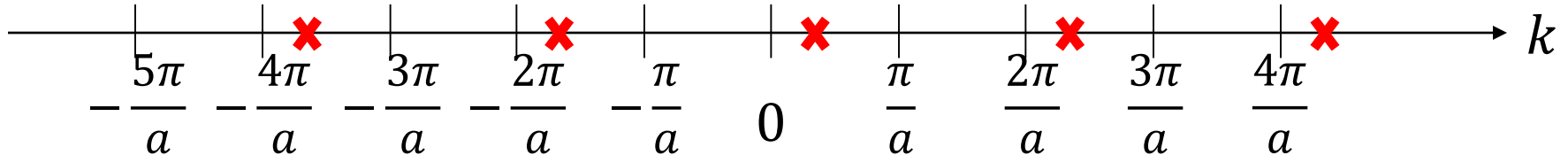


- Square potential
 - (Left) When $V = 0$, it is just a free electron.
 - (Right) When $V \neq 0$, the energy discontinuity is clearly shown.
 - Discontinuity occurs at points such as $\frac{\pi}{a}$, $\frac{2\pi}{a}$, ...



1st Brillouin zone

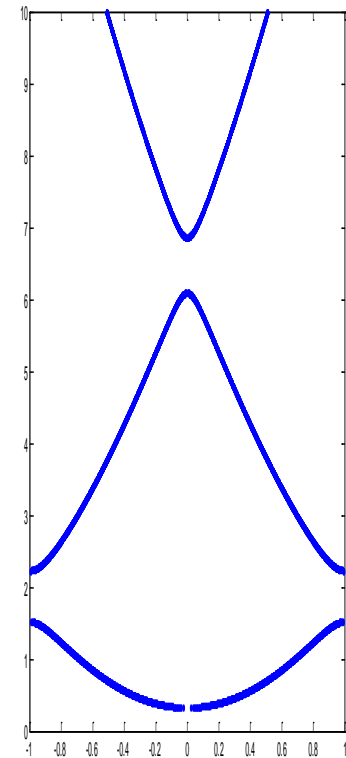
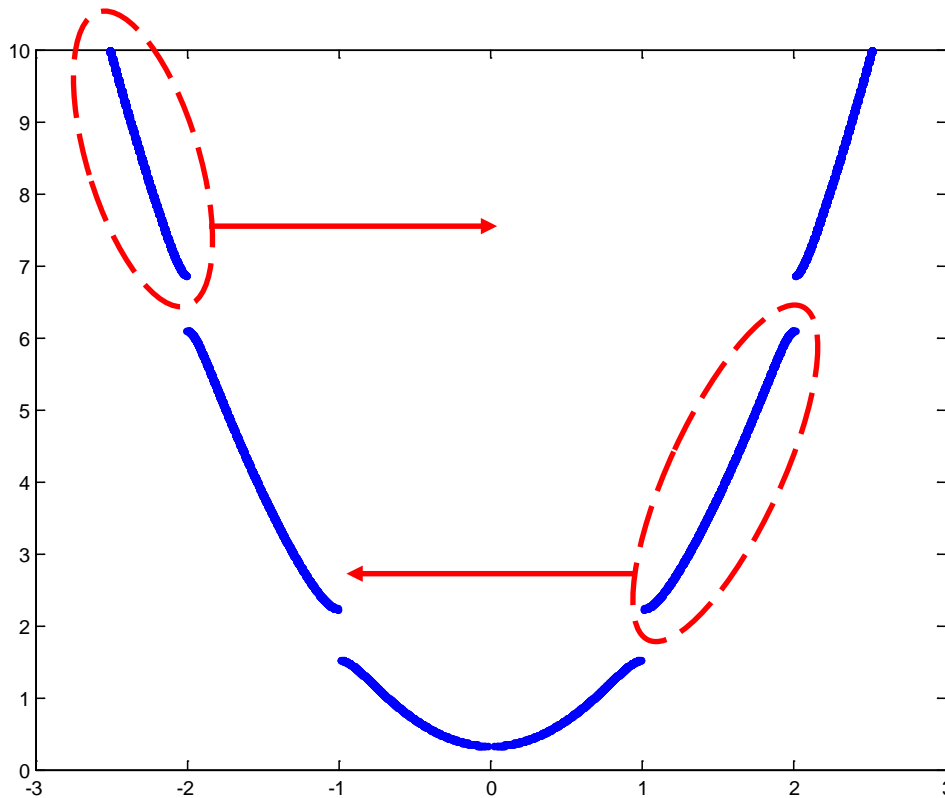
- Shifting the wave number by $\pm \frac{2\pi}{a}$,
 - Following states (Red crosses) are all coupled.



- Then, instead of $(-\infty, \infty)$, a range of $\left[-\frac{\pi}{a}, \frac{\pi}{a}\right]$ is used to represent the wave number axis.
- Such range is called the “1st Brillouin zone.”

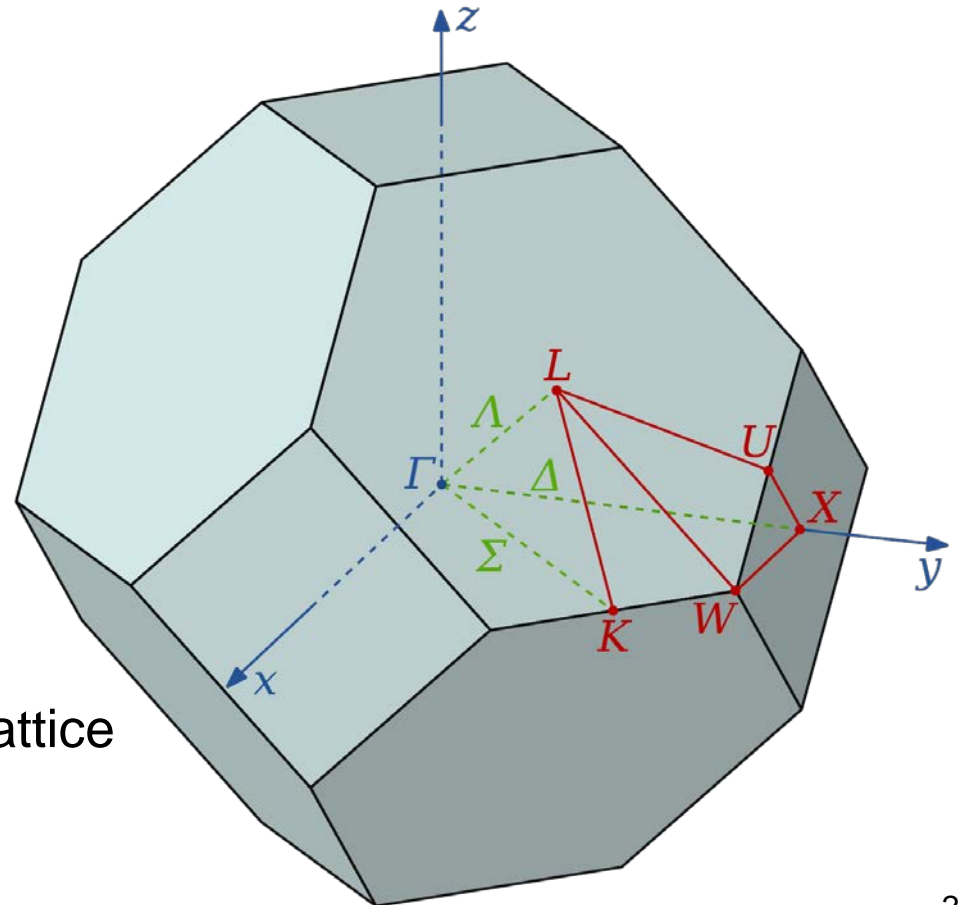
1D case

- Consider the Kronig-Penney model.
 - Bands are clearly identified.



3D case

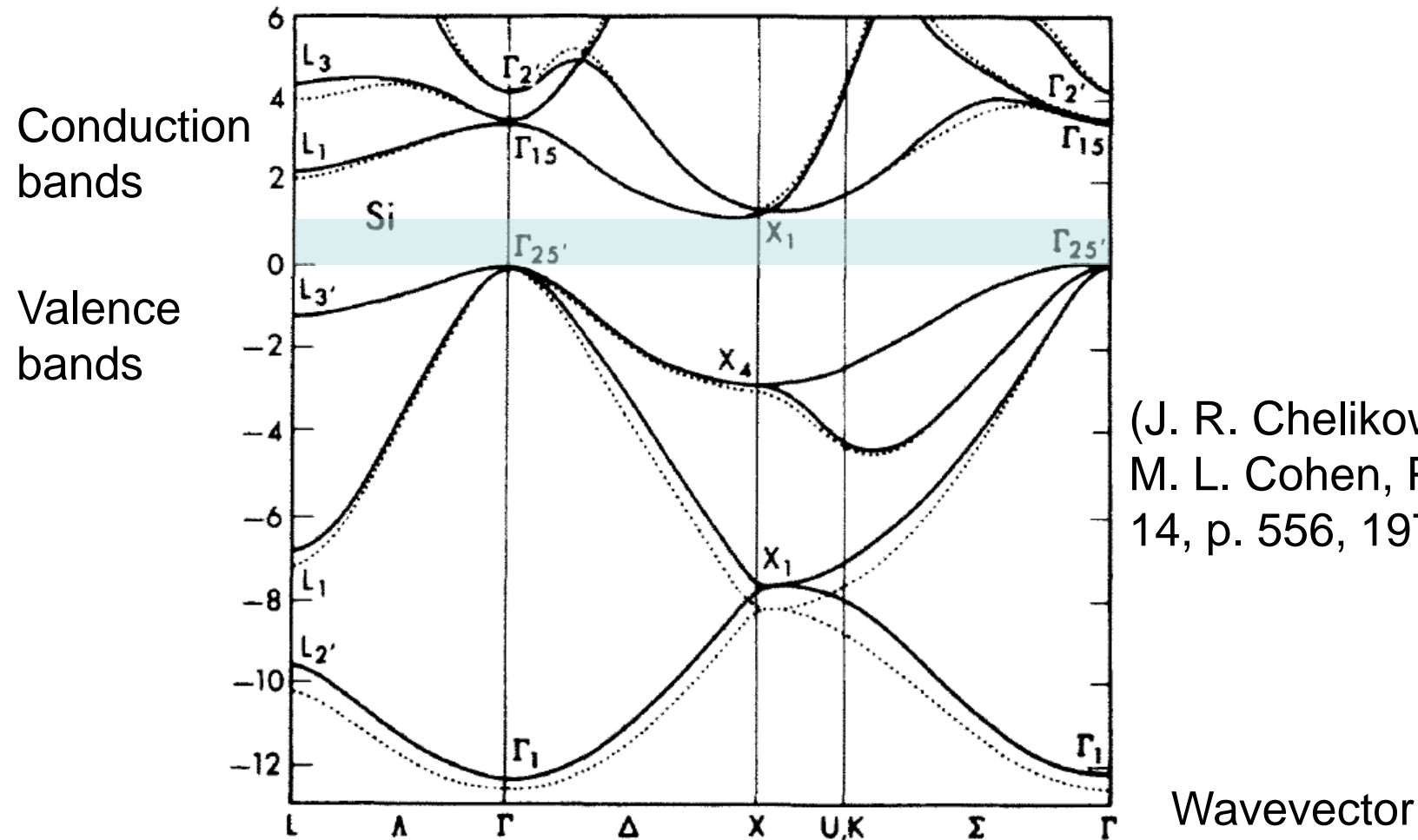
- The 1st Brillouin zone is a volume.
 - How does the Brillouin zone of silicon look like?
 - Silicon has the fcc lattice.



First Brillouin zone of the fcc lattice
(Wikipedia)

Band structure

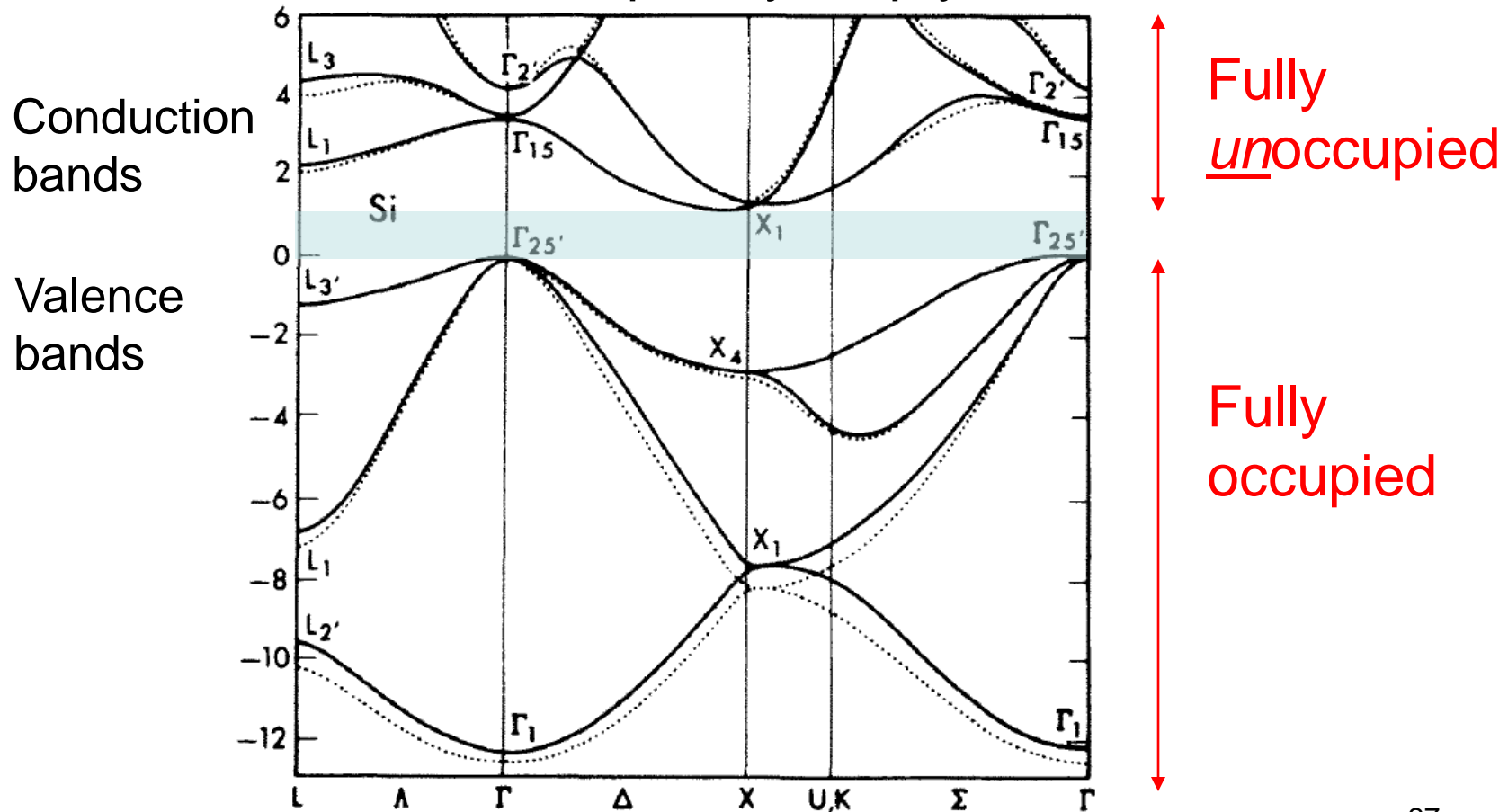
- Band structure of silicon (Band gap ~ 1.12 eV)



(J. R. Chelikowsky and M. L. Cohen, PRB, vol. 14, p. 556, 1976)

At 0 K

- Valence bands are fully filled by electrons.
- Conduction bands are completely empty.



At a non-zero temperature

- Electrons gain thermal energies.
 - A small number of electrons can occupy states in the conduction bands.
 - Example) 5 states in a system. 3 electrons. 1.5 eV
 - What is the ground energy? 1 eV
 - What is the second lowest energy? 0 eV
 - 0.5 eV
 - 1.0 eV

Answers

- Minimizing an additional energy
 - Occupying the lowest energy state in the conduction bands
 - Leaving a “hole” in the valence bands.

1.5 eV

1.5 eV

1 eV

1 eV

0 eV

0 eV

-0.5 eV

-0.5 eV

-1.0 eV

-1.0 eV

Most economic way!



Higher temperature

- Electrons gain even larger thermal energies.
 - More electrons in the conduction bands
 - More holes in the valence bands
- How many electrons are in the conduction bands?
 - The answer is the **intrinsic carrier density**, n_i , at a given temperature.
 - Expression of n_i (Silicon)

$$n_i = 5.2 \times 10^{15} T^{1.5} \exp\left(-\frac{E_g}{2k_B T}\right) \quad (\text{electrons/cm}^3)$$

- Note that k_B is the Boltzmann constant.

Razavi, Example 2.1

- Intrinsic carrier densities at different temperatures
 - At 300 K, 1.08×10^{10} electrons/cm³
 - At 600 K, 1.54×10^{15} electrons/cm³
- What is the meaning?
 - When we have a pure silicon (without any impurities) → Intrinsic
 - The density of both electrons and holes → Carrier density
 - Therefore, for the intrinsic material,
$$n = p = n_i$$

At equilibrium,

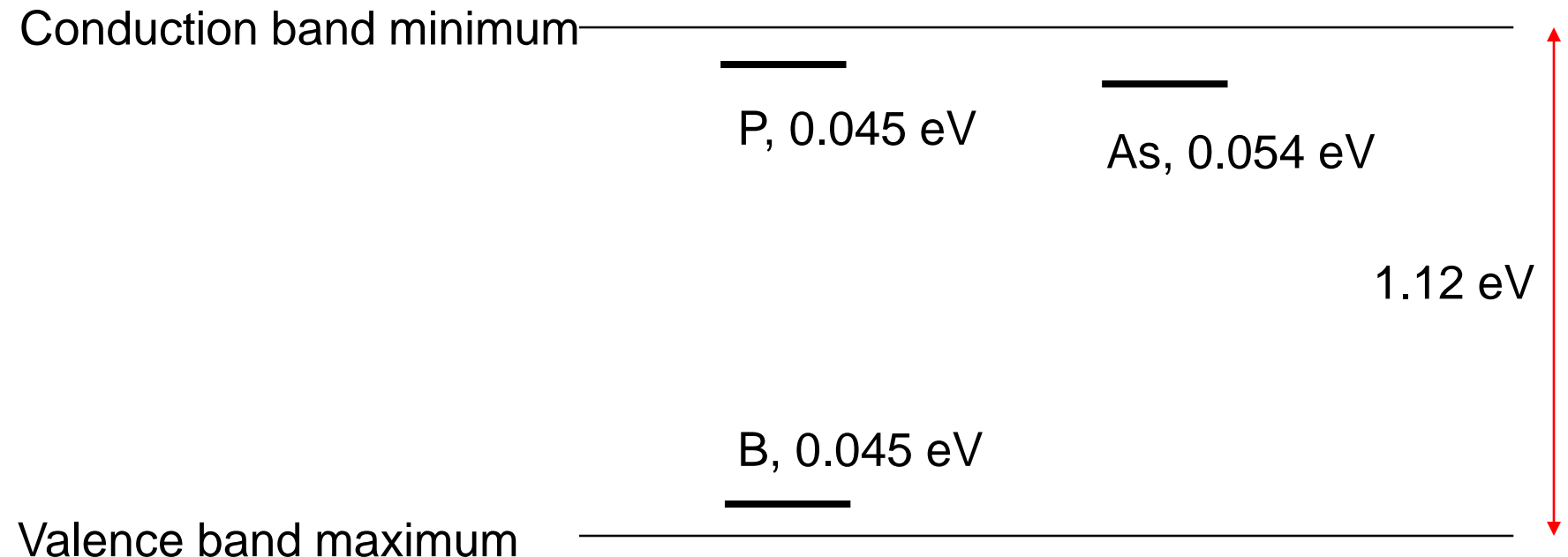
- We have a useful relation.
 - The product between the electron density (n) and the hole density (p) is constant.

$$np = n_i^2$$

- For an intrinsic material, it is immediately verified.
 - How about the EXTRINSIC case?

Energy states

- Donor (Phosphorus and arsenic)
 - Close to the conduction band minimum
- Acceptor (Boron)
 - Close to the valence band maximum



Results of ionization

- Donor (Phosphorus and arsenic)
 - Positively charged
 - An ionized donor contributes an electron in the conduction bands.
- Acceptor (Boron)
 - Negatively charged
 - An ionized acceptor contributes a hole in the valence bands.
- N_D (/cm³) donors? N_D electrons in the conduction bands.
- N_A (/cm³) acceptors? N_A holes in the valence bands.

Numbers

- First of all, the volume density of silicon atoms is $5 \times 10^{22} \text{ cm}^{-3}$.
 - The impurity density is limited to $\sim 2 \times 10^{20} \text{ cm}^{-3}$.
- Various impurity densities
 - 10^{15} cm^{-3} : Almost no impurity
 - 10^{17} cm^{-3} : Low (or moderate) impurity density
 - 10^{19} cm^{-3} : High impurity density (Not extremely high)
 - $2 \times 10^{20} \text{ cm}^{-3}$: High impurity density (Approximately, the maximum limit)

N-type? P-type?

- Semiconductor doped with donors
 - N-type
 - In the n-type semiconductor, we have
$$n \approx N_D > n_i$$
- Semiconductor doped with acceptors
 - P-type
 - In the p-type semiconductor, we have
$$p \approx N_A > n_i$$
- Majority carriers
 - Electrons in the n-type
 - Holes in the p-type
- Minority carriers

Remember $np = n_i^2$.

- (It is valid only at equilibrium.)
- N-type
 - The electron density is almost equal to N_D .
 - The hole density is

$$p \approx \frac{n_i^2}{N_D}$$

- For the p-type material, $n \approx \frac{n_i^2}{N_A}$.
- Razavi, Example 2.3
 - When the donor density is 10^{16} cm^{-3} , the hole density is about 10^4 cm^{-3} .